



200V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C
-200V	25Ω @ V _{GS} = 10V	200mA

Description

This new generation trench MOSFET features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

Active clamping of primary aide MOSFETs in 48 Volt DC-DC converters

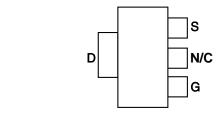
Features and Benefits

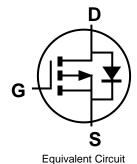
- High Voltage
- Low On-resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3)
- Weight: 0.112 grams (Approximate)







Pin Out - Top

Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP2120G4TA	ZXMP2120	7	12	1,000
ZXMP2120G4TC	ZXMP2120	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT223

ZXMP2120 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5 = 2015) WW or \overline{W} W = Week Code (01~53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-200	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (V _{GS} = 10V; T _A = +25°C) (Note 5)	I _D	-200	mA
Pulsed Drain Current (Note 6)	I _{DM}	-1	A
Pulsed Source Current (Body Diode) (Note 6)	I _{SM}	-1	A

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25°C (Note 5)	D-	2.0	W
Linear Derating Factor	P _D	1.6	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	62.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

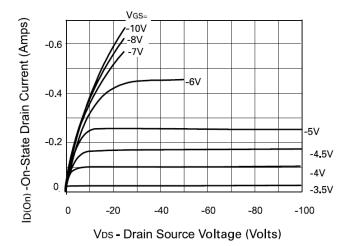
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-200	-	-	V	$V_{GS} = 0V$, $I_D = -1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	-10 -100	μA	$V_{DS} = -200V, V_{GS} = 0V$ $V_{DS} = -160V, V_{GS} = 0V, T = +125$ °C	
Gate-Source Leakage	I _{GSS}	-	-	20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	-1.5	-	-3.5	V	$V_{DS} = V_{GS}$, $I_D = -1mA$	
Static Drain-Source On-Resistance (Note 7)	R _{DS(ON)}	-	-	25	Ω	$V_{GS} = -10V, I_D = -150mA$	
Forward Transconductance (Notes 7 & 8)	g fs	50	-	-	mS	$V_{DS} = -25V, I_{D} = -150mA$	
On-State Drain Current (Note 7)	I _{D(ON)}	-300	-	-	mA	$V_{DS} = -25V, V_{GS} = -10V$	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 8)	C _{iss}	-	-	100	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance (Note 8)	Coss	-	-	25	pF		
Reverse Transfer Capacitance (Note 8)	C _{rss}	-	-	7	pF		
Turn-On Delay Time (Notes 8 & 9)	t _{D(ON)}	-	-	7	ns	V _{DD} = -25V, I _D = -150mA	
Turn-On Rise Time (Notes 8 & 9)	t _R	-	-	15	ns		
Turn-Off Delay Time (Notes 8 & 9)	t _{D(OFF)}	-	-	12	ns		
Turn-Off Fall Time (Notes 8 & 9)	t _F	-	-	15	ns		

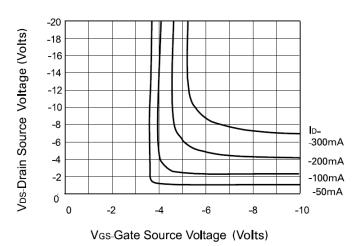
Notes:

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. 6. Repetitive rating pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
- 7. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.
- 9. Switching characteristics are independent of operating junction temperature.

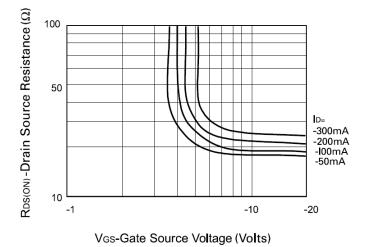




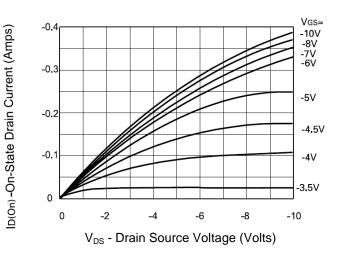
Output Characteristics



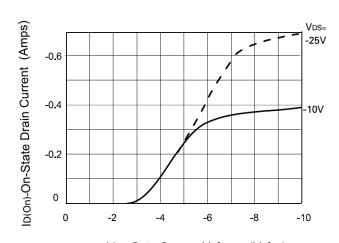
Voltage Saturation Characteristics



On-resistance vs gate-source voltage

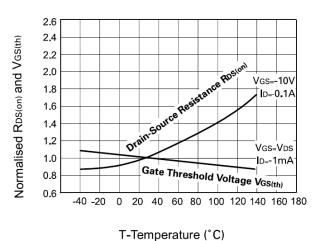


Saturation Characteristics



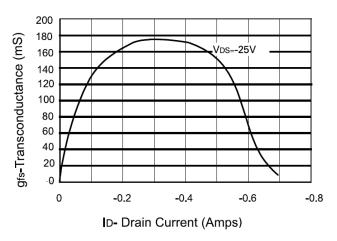
Vgs-Gate Source Voltage (Volts)

Transfer Characteristics



Normalised RDS(on) and VGS(th) vs Temperature

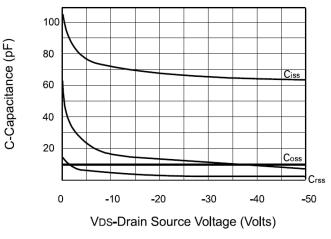


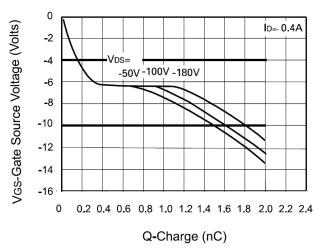


200 180 gfs-Transconductance (mS) 160 140 120 VDS=-25V 100 80 60 40 20 0 0 **-**2 -6 -8 -10 VGS-Gate Source Voltage (Volts)

Transconductance v drain current

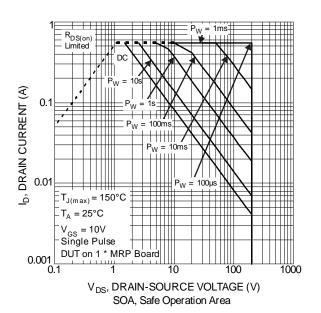
Transconductance v gate-source voltage





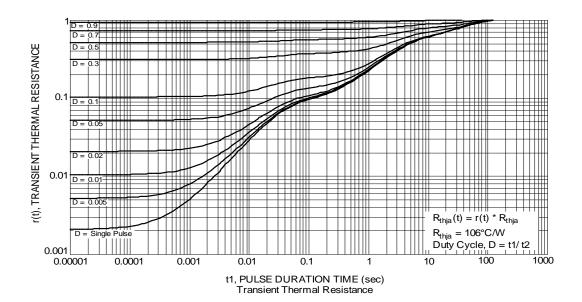
Capacitance v drain-source voltage

Gate charge v gate-source voltage



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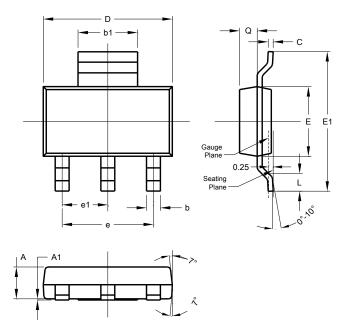






Package Outline Dimensions

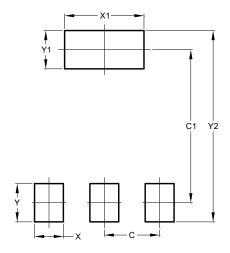
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	2.30			
C1	6.40			
Х	1.20			
X1	3.30			
Υ	1.60			
Y1	1.60			
Y2	8.00			

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